

**Notice of References Cited**

Application/Control No.

10/567,729

Applicant(s)/Patent Under  
Reexamination  
KOJIMA ET AL.

Examiner

SARAH K. SALERNO

Art Unit

2814

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,165,874	12-2000	Powell et al.	438/478
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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	P					
	Q					
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	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Steckl et al. ("Epitaxial Growth of B-SiC on Si by RTCVD with C3H8 and SiH4"; IEEE Transactions on Electron Devices Vol. 39, No. 1, Jan 1992 pages 64-73)
	V	Hallin et al. "Homoepitaxial on-axis growth of 4H- and 6H-SiC by CVD" Materials Science Forum Vols. 457-460 (2004) pp. 193-196
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.